



Seminarankündigung

Dienstag, 24. April 2018

14:00 Uhr

WSI, Seminarraum S 101

“2D dichalcogenide electronic materials and valley/spin devices”

The band structure of transition metal dichalcogenides (TMDCs) with valence band edges at different locations in the momentum space could be harnessed to build devices that operate relying on the valley degree of freedom. To realize such valleytronic devices, it is necessary to control and manipulate the charge density in these valleys. In my talk, I will present our most recent efforts in this direction. In the first part, I will present our direct measurements of the conduction band splitting in MoS₂ quantum point contacts. In the second, I will present our recent results on the electrical manipulation of interlayer excitons in TMDC heterostructures.

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